



# UNISONIC TECHNOLOGIES CO., LTD

## 7N60A

Power MOSFET

7 Amps, 600/650 Volts  
N-CHANNEL MOSFET

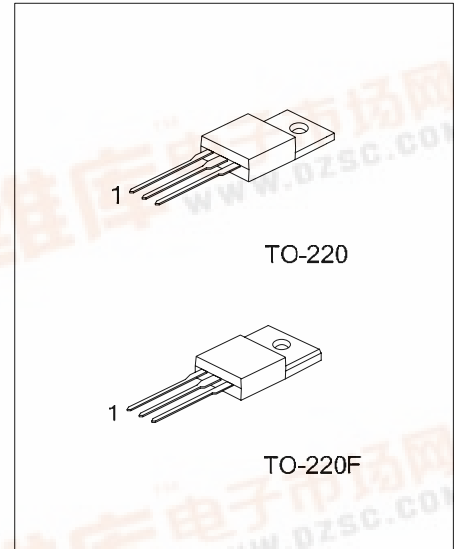
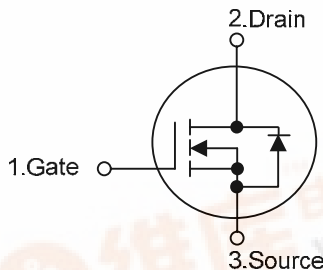
### DESCRIPTION

The UTC 7N60A is a high voltage N-Channel enhancement mode power field effect transistors and is designed to have minimize on-state resistance , provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. This power MOSFET is well suited for high efficiency switch mode power supply.

### FEATURES

- \*  $R_{DS(ON)} = 1.2\Omega @ V_{GS} = 10V$
- \* Ultra low gate charge (typical 28 nC )
- \* Low reverse transfer Capacitance ( $C_{RSS} =$  typical 12 pF )
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness

### SYMBOL



\*Pb-free plating product number:7N60AL

### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
7N60A-x-TA3-T	7N60AL-x-TA3-T	TO-220	G	D	S	Tube
7N60A-x-TF3-T	7N60AL-x-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>7N60AL-x-TA3-T</p>	<ul style="list-style-type: none"> <li>(1)Packing Type</li> <li>(2)Package Type</li> <li>(3)Drain-Source Voltage</li> <li>(4)Lead Plating</li> </ul>	<ul style="list-style-type: none"> <li>(1) T: Tube</li> <li>(2) TA3: TO-220, TF3: TO-220F</li> <li>(3) A: 600V, B: 650V</li> <li>(4) L: Lead Free Plating, Blank: Pb/Sn</li> </ul>
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# 7N60A

## Power MOSFET

### ■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage	7N60A-A	$V_{DSS}$	600	V
	7N60A-B		650	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Avalanche Current (Note 1)		$I_{AR}$	7	A
Continuous Drain Current	$T_C = 25^\circ C$	$I_D$	7	A
	$T_C = 100^\circ C$		3.2	A
Pulsed Drain Current (Note 1)		$I_{DM}$	28	A
Avalanche Energy	Single Pulsed (Note 2)	$E_{AS}$	330	mJ
	Repetitive Limited by $T_{J(MAX)}$	$E_{AR}$	7.5	mJ
Power Dissipation		$P_D$	30	W
Junction Temperature		$T_J$	+150	
Operating Temperature		$T_{OPR}$	-55 ~ +150	
Storage Temperature		$T_{STG}$	-55 ~ +150	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.  
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

### ■ THERMAL DATA

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient	$\theta_{JA}$			62.5	$^\circ C/W$
Junction-to-Case	$\theta_{JC}$			4.16	$^\circ C/W$

### ■ ELECTRICAL CHARACTERISTICS ( $T_C = 25$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	7N60A-A	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	600		V
	7N60A-B			650		V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 600V, V_{GS} = 0V$			1	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{DS} = \pm 30V, V_{GS} = 0V$			$\pm 100$	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 3.5A$ (Note 4)		1.0	1.2	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=25V, V_{GS}=0V, f=1.0$ MHz		950	1430	pF
Output Capacitance	$C_{OSS}$			85	130	pF
Reverse Transfer Capacitance	$C_{RSS}$			12	18	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=300V, I_D=7A, R_G=25\Omega$ (Note 3, 4)		16		ns
Turn-On Rise Time	$t_R$			60		ns
Turn-Off Delay Time	$t_{D(OFF)}$			80		ns
Turn-Off Fall Time	$t_F$			65		ns
Total Gate Charge	$Q_G$	$V_{DS}=300V, I_D=7A, V_{GS}=10$ V (Note 3, 4)		28	42	nC
Gate-Source Charge	$Q_{GS}$			5.5	8.3	nC
Gate-Drain Charge	$Q_{GD}$			11	17	nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Drain-Source Diode Forward Voltage (Note 4)	$V_{SD}$	$V_{GS} = 0V, I_S = 7A$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				7	A
Maximum Pulsed Drain-Source Diode Forward Current (Note 1)	$I_{SM}$				28	A
Reverse Recovery Time	$t_{RR}$	$V_{GS} = 0V, I_S = 7A,$		365		ns
Reverse Recovery Charge	$Q_{RR}$	$dI_F / dt = 100A/\mu s$		4.23		$\mu C$

■ ELECTRICAL CHARACTERISTICS(Cont.)

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 9.8\text{mH}$ ,  $I_{AS} = 7\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 27\ \Omega$
3. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
4. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

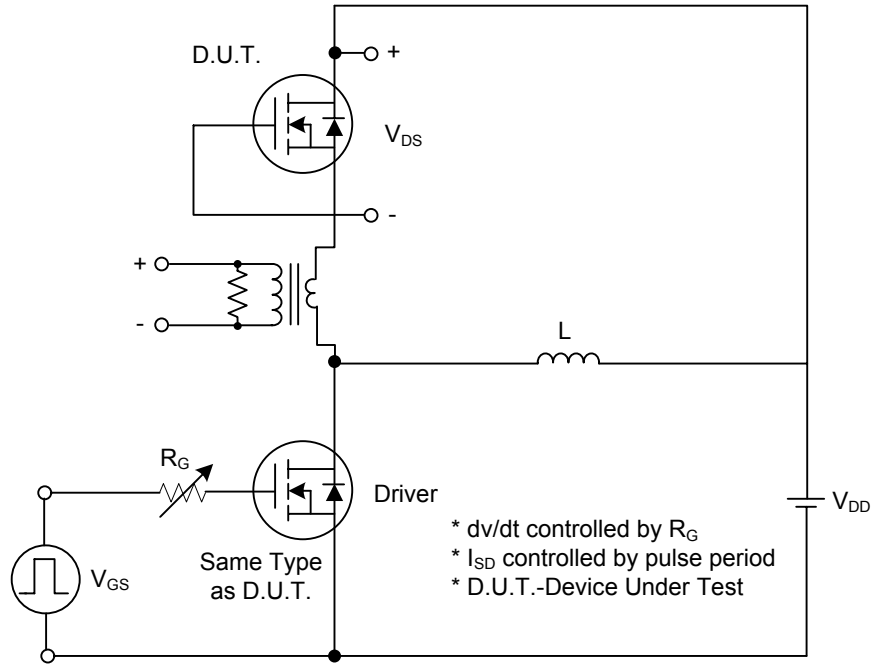


Fig. 1A Peak Diode Recovery  $dv/dt$  Test Circuit

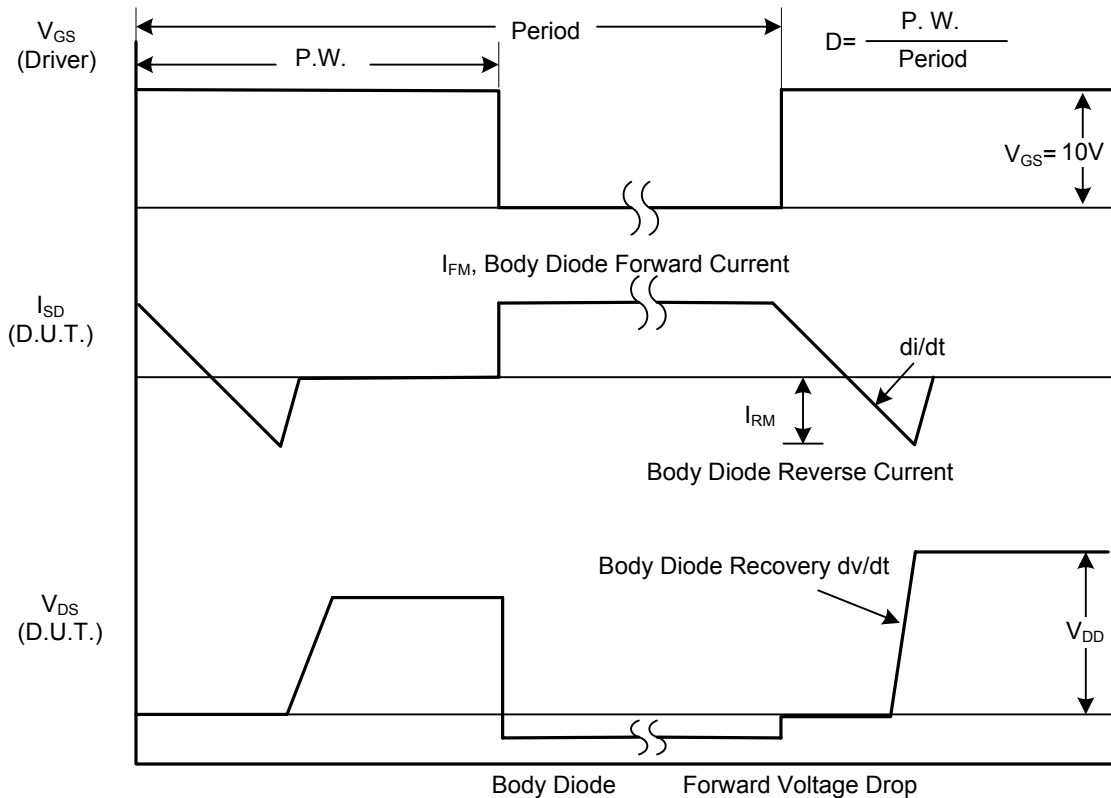


Fig. 1B Peak Diode Recovery  $dv/dt$  Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

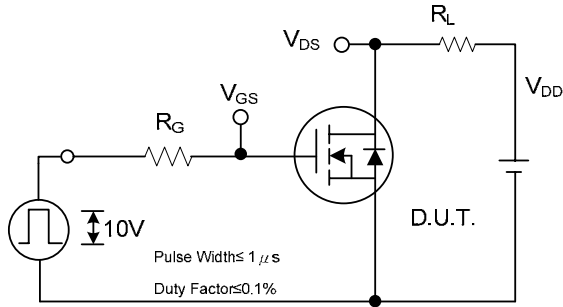


Fig. 2A Switching Test Circuit

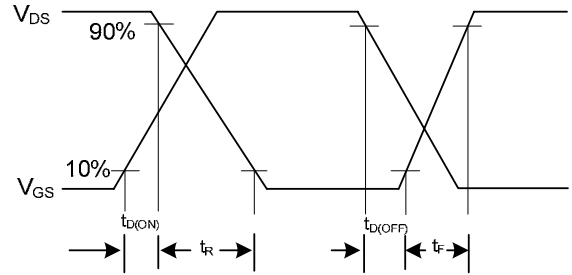


Fig. 2B Switching Waveforms

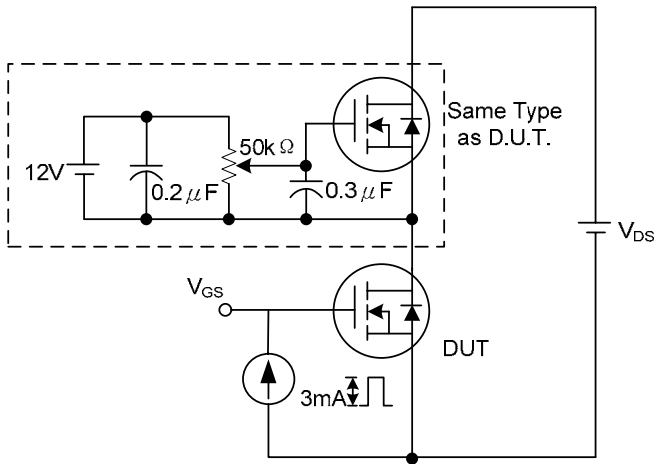


Fig. 3A Gate Charge Test Circuit

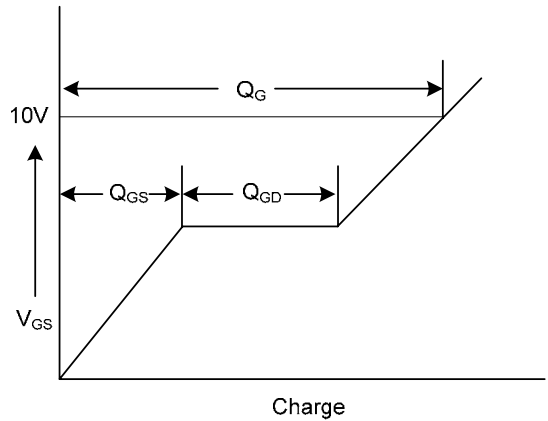


Fig. 3B Gate Charge Waveform

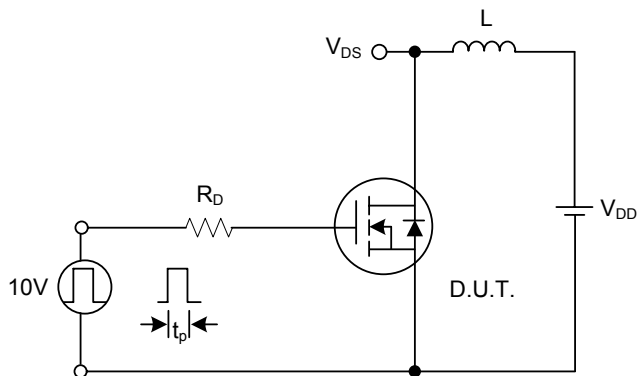


Fig. 4A Unclamped Inductive Switching Test Circuit

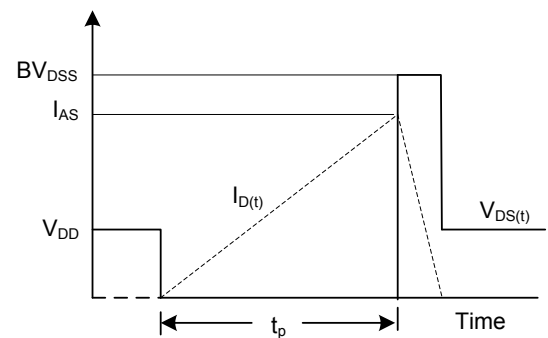
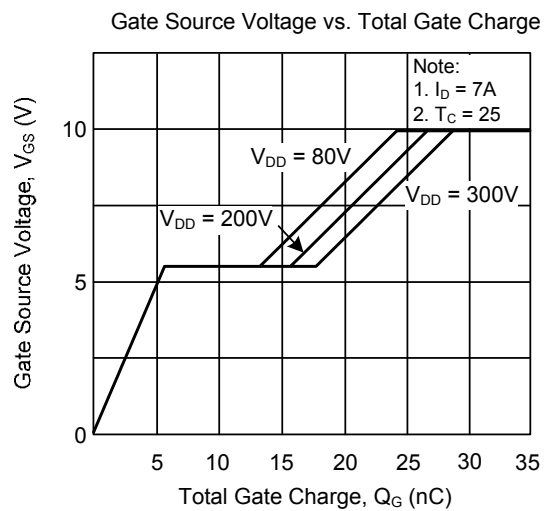
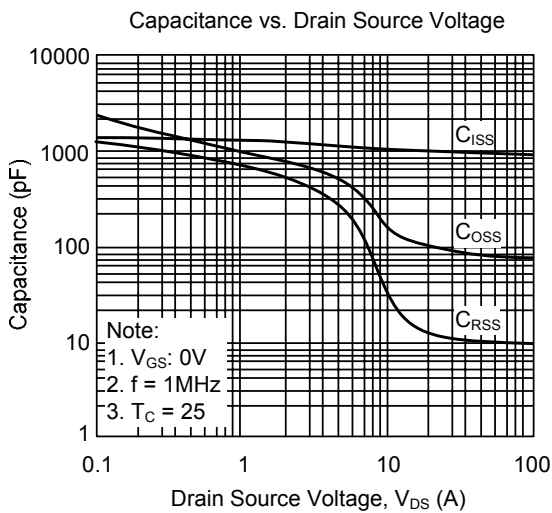
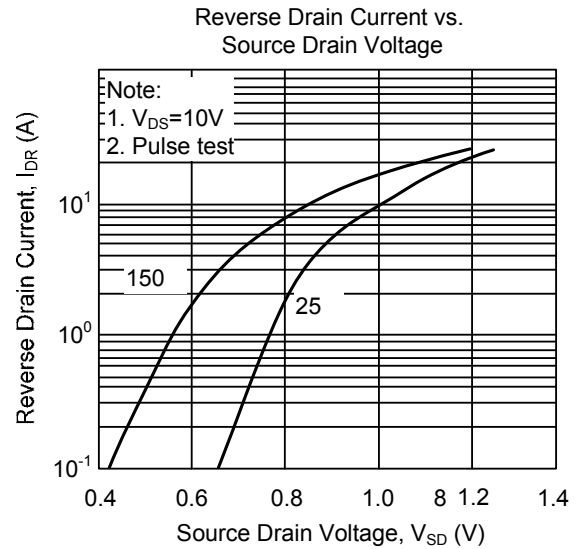
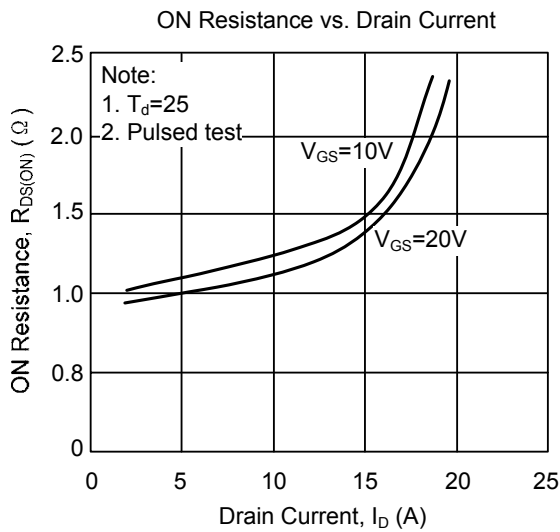
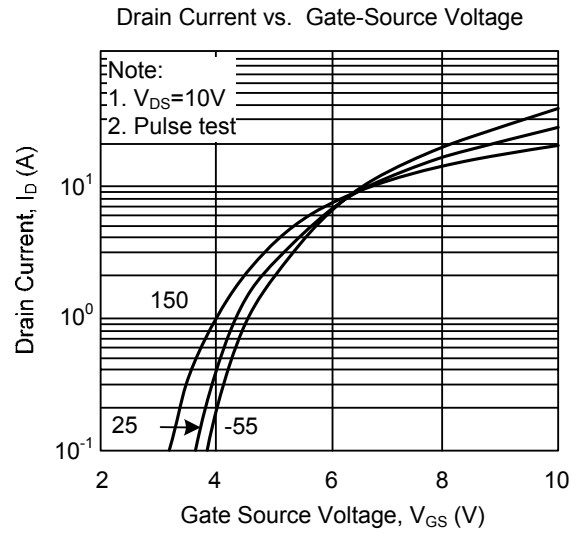
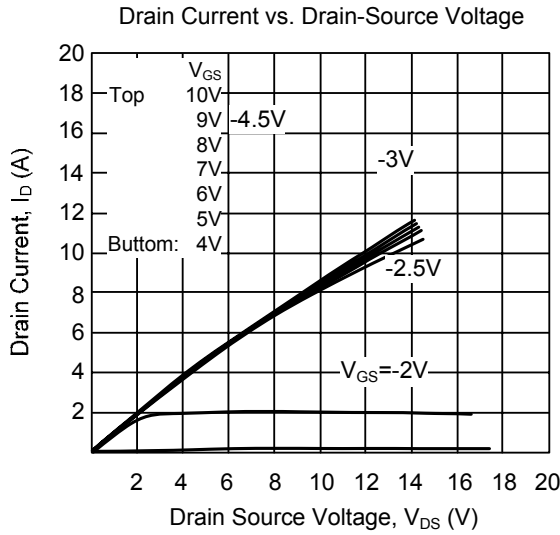
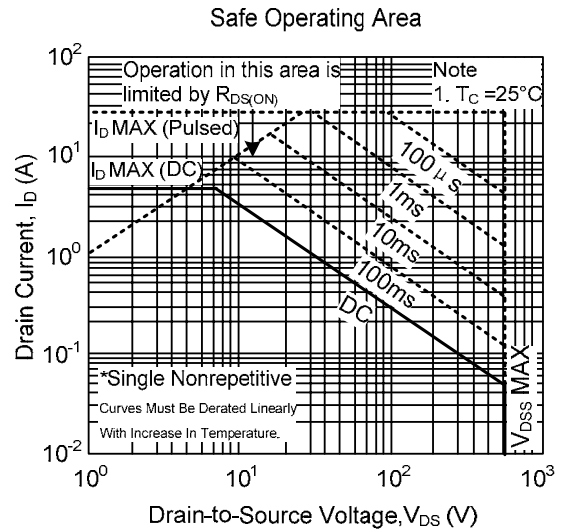
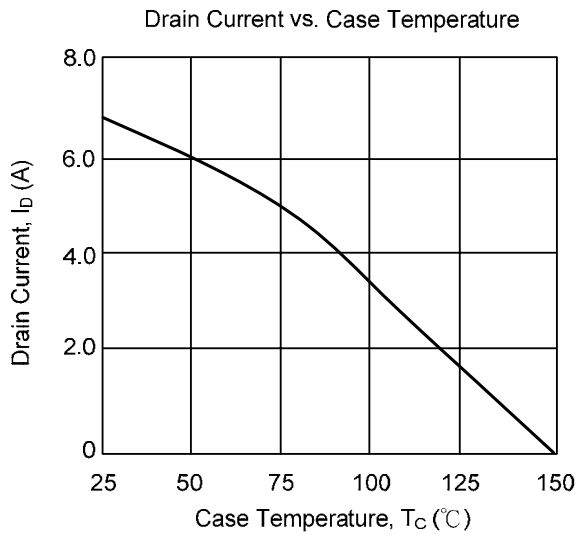
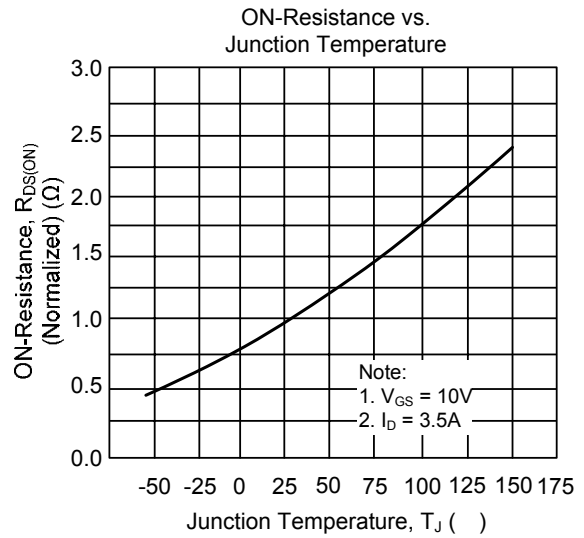
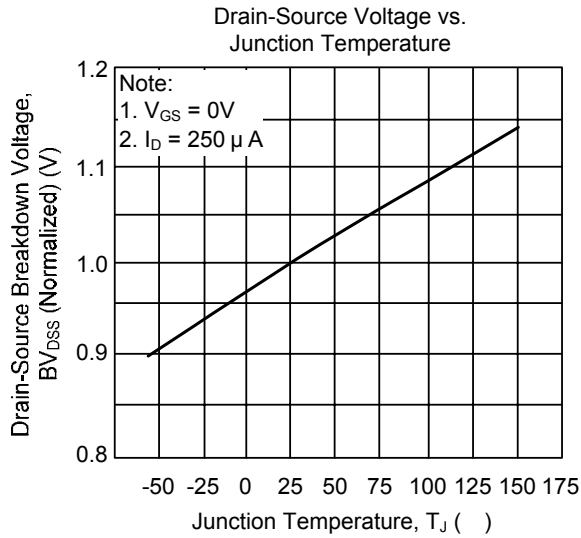


Fig. 4B Unclamped Inductive Switching Waveforms

## TYPICAL CHARACTERISTICS



## TYPICAL CHARACTERISTICS (Cont.)



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